IN THE CLAIMS

1. (Currently Amended) A method of forming a gate oxide on a transistor body region, comprising:

evaporation depositing a metal alloy layer on the body region wherein at least a portion of the alloy layer is amorphous; and

oxidizing the metal alloy layer to form a metal oxide layer on the body region.

- 2. (Original) The method of claim 1, wherein evaporation depositing the metal alloy layer includes evaporation depositing cobalt and titanium.
- 3. (Original) The method of claim 1, wherein evaporation depositing the metal alloy layer includes evaporation depositing by electron beam evaporation.
- 4. (Original) The method of claim 3, wherein electron beam evaporation depositing the metal alloy layer includes electron beam evaporation of a single metal alloy target.
- 5. (Original) The method of claim 1, wherein evaporation depositing the metal alloy layer includes evaporation depositing at an approximate substrate temperature range of 100 150° C.
- 6. (Original) The method of claim 1, wherein oxidizing the metal alloy layer includes oxidizing at a temperature of approximately 400° C.
- 7. (Original) The method of claim 1, wherein oxidizing the metal alloy layer includes oxidizing with atomic oxygen.
- 8. (Original) The method of claim 1, wherein oxidizing the metal alloy layer includes oxidizing using a krypton (Kr)/oxygen (O₂) mixed plasma process.



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9. (Currently Amended) A method of forming a gate oxide on a transistor body region, comprising:

evaporation depositing a metal alloy layer on the body region wherein at least a portion of the alloy layer is amorphous; and

oxidizing the metal alloy layer using a krypton(Kr)/oxygen (O₂) mixed plasma process to form a metal oxide layer on the body region.

- 10. (Original) The method of claim 9, wherein evaporation depositing the metal alloy layer includes evaporation depositing cobalt and titanium.
- 11. (Original) The method of claim 9, wherein evaporation depositing the metal alloy layer includes evaporation depositing by electron beam evaporation.
- 12. (Original) The method of claim 11, wherein electron beam evaporation depositing the metal alloy layer includes electron beam evaporation of a single metal alloy target.
- 13. (Original) The method of claim 9, wherein evaporation depositing the metal alloy layer includes evaporation depositing at an approximate substrate temperature range of 150 400 °C.

14. - 54. (Previously Withdrawn)

55. (Currently Amended) A method of forming a gate oxide on a transistor body region, comprising:

electron beam evaporation depositing a metal alloy layer on the body region wherein at least a portion of the alloy layer is amorphous; and

oxidizing the metal alloy layer to form a metal oxide layer on the body region.

56. (New) A method of forming a gate oxide on a transistor body region, comprising: evaporation depositing an alloy layer including cobalt and titanium on the body region;

oxidizing the metal alloy layer to form a metal oxide layer on the body region.

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and

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- 57. (New) The method of claim 56, wherein oxidizing the metal alloy layer includes oxidizing with atomic oxygen.
- 58. (New) The method of claim 56, wherein oxidizing the metal alloy layer includes oxidizing using a krypton (Kr)/oxygen (O₂) mixed plasma process.
- 59. (New) A method of forming a gate oxide on a transistor body region, comprising: evaporation depositing an alloy layer including cobalt and titanium on the body region; and

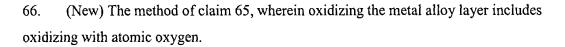


- oxidizing the metal alloy layer using a krypton(Kr)/oxygen (O₂) mixed plasma process to form a metal oxide layer on the body region.
- 60. (New) The method of claim 59, wherein evaporation depositing the metal alloy layer includes evaporation depositing by electron beam evaporation.
- 61. (New) The method of claim 59, wherein electron beam evaporation depositing the metal alloy layer includes electron beam evaporation of a single metal alloy target.
- 62. (New) A method of forming a gate oxide on a transistor body region, comprising: evaporation depositing an alloy layer including cobalt and titanium on the body region wherein at least a portion of the alloy layer is amorphous; and oxidizing the metal alloy layer to form a metal oxide layer on the body region.
- 63. (New) The method of claim 62, wherein evaporation depositing the metal alloy layer includes evaporation depositing by electron beam evaporation.
- 64. (New) The method of claim 62, wherein electron beam evaporation depositing the metal alloy layer includes electron beam evaporation of a single metal alloy target.

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65. (New) A method of forming a gate oxide on a transistor body region, comprising:
evaporation depositing an alloy layer including cobalt and titanium on the body region
wherein at least a portion of the alloy layer is amorphous; and

oxidizing the metal alloy layer using a krypton(Kr)/oxygen (O₂) mixed plasma process to form a metal oxide layer on the body region.



67. (New) The method of claim 65, wherein oxidizing the metal alloy layer includes oxidizing using a krypton (Kr)/oxygen (O₂) mixed plasma process.

